PRELIMINARY DATA SHEET

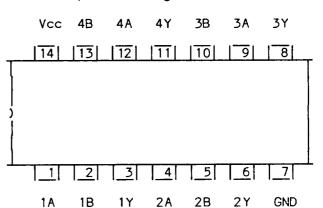
ADVANCED LOW-POWER SCHOTTKY TTL

TYPES SN54ALS903 and SN74ALS903 QUAD 2-INPUT NAND BUFFERS with OPEN COLLECTOR OUTPUTS

- * QUAD 2-INPUT NAND BUFFERS w/O.C.
 OUTPUTS
- * ADVANCED OXIDE-ISOLATED, ION-IMPLANTED SCHOTTKY TTL PROCESS
- * FUNCTIONALLY and PIN-for-PIN COMPATIBLE with TTL COUNTERPART
- * IMPROVED AC PERFORMANCE over LS COUNTERPART
- * HALF the POWER of LS COUNTERPART
- * IMPROVED INPUT THRESHOLD VOLTAGE
- * IMPROVED LINE RECEIVING CHARACTER-ISTICS

ELECTRICAL PINOUT

positive logic: Y=AB



This advanced low-power Schottky device has been fabricated by an advanced oxide-isolated, ion-implanted Schottky TTL process developed by TI. The major benefit of this process is the improvement of the speed-power product by the reduction of parasitic and side-wall capacitance and enhanced $f_{\uparrow}.$ The ALS family features the same output drive characteristics as the LS family.

switching characteristics Vcc=5V.Ta=25°C.CI=50pF.RI=667ohms

1		SN54ALS903	SN74ALS903		
	PARAMETER	min typ max	min typ max	UNIT	
tplh	Propagation delay time, low-to-high-level output	14.5	14.5	ns	
†ph1	Propagation delay time, high-to-low-level output	10.0	10.0	ns	

supply current over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS	SN54ALS903		SN74ALS903		1 1
			+,,,	may	+40	mav	UNIT
 			 †ур	max	Тур	max	
lcch	Supply current, outputs high	Vcc=MAX,Vi=OV	.86	2•1	•86	2.1	mΑ
Iccl	Supply current, outputs low	Vcc=MAX, Vi=4.5V	4.0	6.8	4.0	6.8	mA

OCT 1980